

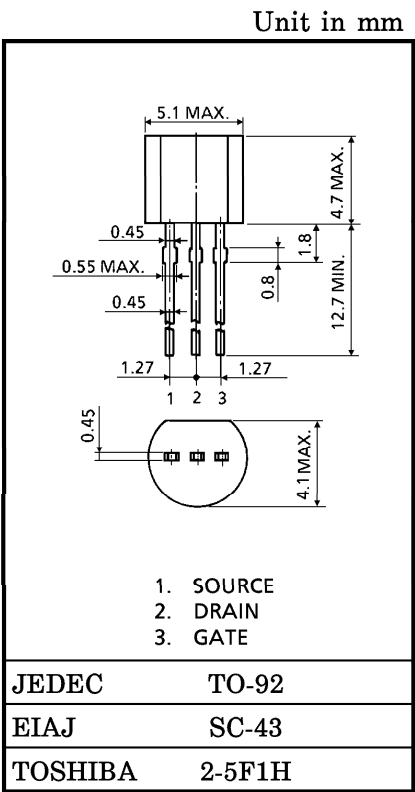
2SJ148

HIGH SPEED SWITCHING APPLICATIONS
ANALOG SWITCH APPLICATIONS
INTERFACE APPLICATIONS

- Excellent Switching Time : $t_{on} = 14ns$ (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}| = 100mS$ (Min.)
- Low On Resistance : $R_{DS(ON)} = 1.3\Omega$ (Typ.)
- Enhancement-Mode
- Complementary to 2SK982

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Drain-Source Voltage		V_{DSS}	-60	V
Gate-Source Voltage		V_{GSS}	± 20	V
Drain Current	DC	I_D	-200	mA
	Pulse	I_{DP}	-800	
Drain Power Dissipation (Ta = 25°C)		P_D	400	mW
Channel Temperature		T_{ch}	150	°C
Storage Temperature Range		T_{stg}	-55~150	°C

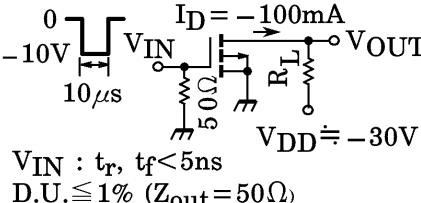


Weight : 0.21g (Typ.)

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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		I_{GSS}	$V_{GS} = \pm 10V, V_{DS} = 0$	—	—	± 100	nA
Drain Cut-off Current		I_{DSS}	$V_{DS} = -60V, V_{GS} = 0$	—	—	-10	μA
Drain-Source Breakdown Voltage		$V_{(BR) DSS}$	$I_D = -1mA, V_{GS} = 0$	-60	—	—	V
Gate Threshold Voltage		V_{th}	$V_{DS} = -10V, I_D = -1mA$	-2	—	-3.5	V
Forward Transfer Admittance		$ Y_{fs} $	$V_{DS} = -10V, I_D = -50mA$	100	—	—	mS
Drain-Source ON Resistance		$R_{DS(ON)}$	$I_D = -50mA, V_{GS} = -10V$	—	1.3	2.0	Ω
Drain-Source ON Voltage		$V_{DS(ON)}$	$I_D = -50mA, V_{GS} = -10V$	—	-65	-100	mV
Input Capacitance		C_{iss}	$V_{DS} = -10V, V_{GS} = 0, f = 1MHz$	—	73	85	pF
Reverse Transfer Capacitance		C_{rss}	$V_{DS} = -10V, V_{GS} = 0, f = 1MHz$	—	15	22	pF
Output Capacitance		C_{oss}	$V_{DS} = -10V, V_{GS} = 0, f = 1MHz$	—	48	60	pF
Switching Time	Rise Time	t_r	 $I_D = -100mA$ $V_{IN} : t_r, t_f < 5ns$ $D.U. \leq 1\% (Z_{out} = 50\Omega)$ $V_{DD} = -30V$	—	8	—	ns
	Turn-on Time	t_{on}		—	14	—	
	Fall Time	t_f		—	35	—	
	Turn-off Time	t_{off}		—	100	—	

This transistor is the electrostatic sensitive device. Please handle with caution.

